SN74AHC1G08 シングル 2 入力、正論理 AND ゲート

1 特長

- 動作範囲：2V ~ 5.5V
- 最大 t_{pd} 7ns (5V 時)
- 低消費電力、最大 I_{CC} 10µA
- ±8mA の出力駆動能力 (5V 時)
- 全入力でのシュミット・トリガ・アクションにより、低速の入力立ち上がり / 立ち下がり時間を許容
- JESD 17 準拠で 250mA 超のラッチアップ性能

2 アプリケーション

- バーコード・スキャナ
- ケーブル・ソリューション
- eBook (電子書籍)
- 組み込み用 PC
- フィールド・トランスミッタ：温度センサ、圧力センサ
- 指紋認証
- HVAC：暖房、換気、空調
- ネットワーク接続ストレージ (NAS)
- サーバーのマザーボードおよび PSU
- ソフトウェア定義無線 (SDR)
- テレビ：高解像度 (HDTV)、LCD、デジタル
- ビデオ通信システム
- ワイヤレス・データ・アクセス・カード、ヘッドセット、キーボード、マウス、LAN カード

3 概要

SN74AHC1G08 デバイスはシングル 2 入力正論理 AND ゲートです。デバイスは、ブール関数 Y = A ● B つまり、$Y = \overline{A + B}$ を正論理で実行します。

パッケージ情報

部品番号	パッケージ (1)	パッケージ・サイズ (2)	本体サイズ (3)
SN74AHC1G08	DBV (SOT-23、5)	2.9mm × 2.8mm	2.9mm × 1.6mm
	DCK (SC-70、5)	2mm × 2.1mm	2mm × 1.25mm
	DRL (SOT、5)	1.6mm × 1.6mm	1.6mm × 1.2mm

(1) 利用可能なすべてのパッケージについては、データシートの末尾にある注文情報を参照してください。
(2) パッケージ・サイズ (長さ × 幅) は公称値で、該当する場合はピンも含まれます。
(3) 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。

論理図 (正論理)

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4 Pin Configuration and Functions

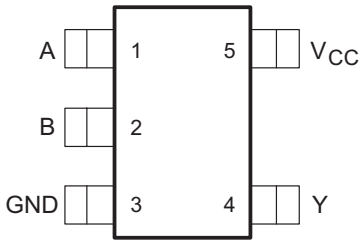


図 4-1. DBV Package 5-Pin SOT-23 Top View

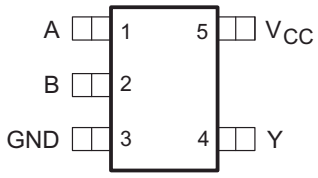
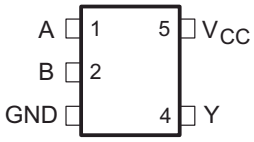


図 4-2. DCK Package 5-Pin SC70 Top View



See mechanical drawings for dimensions (in *セクション 11*).

図 4-3. DRL Package 5-Pin SOT Top View

表 4-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NO.	NAME		
1	A	I	Data Input
2	B	I	Data Input
3	GND	—	Ground
4	Y	O	Data Output
5	VCC	—	Power

(1) Signal Types: I = Input, O = Output, I/O = Input or Output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	7	V
V_I	Input voltage(2)		–0.5	7	V
V_O	Output voltage(2)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–20	mA
I_{OK}	Output clamp current	V_O < 0 or V_O > V_{CC}		±20	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		±25	mA
	Continuous current through V_{CC} or GND			±50	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		V
		V_{CC} = 3 V	2.1		
		V_{CC} = 5.5 V	3.85		
V_{IL}	Low-level Input voltage	V_{CC} = 2 V		0.5	V
		V_{CC} = 3 V		0.9	
		V_{CC} = 5.5 V		1.65	
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50	µA
		V_{CC} = 3.3 V ± 0.3 V		–4	mA
		V_{CC} = 5 V ± 0.5 V		–8	
I_{OL}	Low-level output current	V_{CC} = 2 V		50	µA
		V_{CC} = 3.3 V ± 0.3 V		4	mA
		V_{CC} = 5 V ± 0.5 V		8	
Δt/Δv	Input transition rise or fall rate	V_{CC} = 3.3 V ± 0.3 V		100	ns/V
		V_{CC} = 5 V ± 0.5 V		20	

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
T_A	Operating free-air temperature	–55	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.4 Thermal Information

THERMAL METRIC(1)		SN74AHC1G08			UNIT
		DBV (SOT-23)	DCK (SC70)	DRL (SOT)	
		5 PINS	5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	278	289.2	142	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	T_A = 25°C			T_A = –55°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	
V_{OH}	High level output voltage	I_{OH} = –50 µA	2 V	1.9	2		1.9		V
			3 V	2.9	3		2.9		
			4.5 V	4.4	4.5		4.4		
		I_{OH} = –4 mA	3 V	2.58			2.48		
		I_{OH} = –8 mA	4.5 V	3.94			3.8		
V_{OL}	Low level output voltage	I_{OL} = 50 µA	2 V			0.1		0.1	V
			3 V			0.1		0.1	
			4.5 V			0.1		0.1	
		I_{OL} = 4 mA	3 V			0.36		0.44	
		I_{OL} = 8 mA	4.5 V			0.36		0.44	
I_I	Input leakage current	V_I = 5.5 V or GND	0 V to 5.5 V			±0.1		±1	µA
I_{CC}	Supply current	V_I = V_{CC} or GND, I_O = 0	5.5 V			1		10	µA
C_i	Input Capacitance	V_I = V_{CC} or GND	5 V		4	10		10	pF

5.6 Switching Characteristics, V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	OUTPUT CAPACITANCE	T_A = 25°C			T_A = –40°C to 85°C		T_A = –55°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	Y	C_L = 15 pF		6.2	8.8	1	10.5	1	11	ns
t_{PHL}					6.2	8.8	1	10.5	1	11	
t_{PLH}	A or B	Y	C_L = 50 pF		8.7	12.3	1	14	1	14.5	ns
t_{PHL}					8.7	12.3	1	14	1	14.5	

5.7 Switching Characteristics, V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Load Circuit and Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	OUTPUT CAPACITANCE	T_A = 25°C			T_A = –40°C to 85°C		T_A = –55°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	Y	C_L = 15 pF		4.3	5.9	1	7	1	7.5	ns
t_{PHL}					4.3	5.9	1	7	1	7.5	
t_{PLH}	A or B	Y	C_L = 50 pF		5.8	7.9	1	9	1	9.5	ns
t_{PHL}					5.8	7.9	1	9	1	9.5	

5.8 Operating Characteristics

V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance	No load,	f = 1 MHz	18	pF

5.9 Typical Characteristics

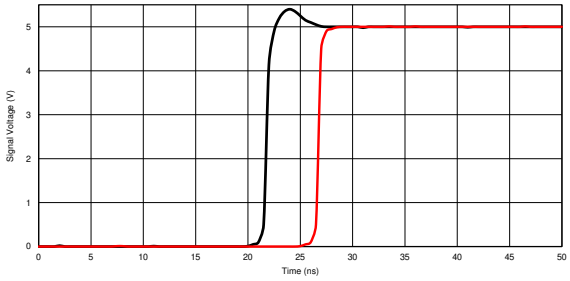
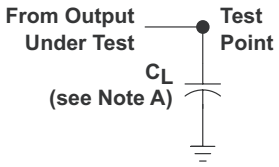
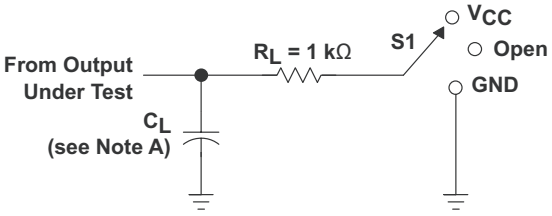


図 5-1. Response Time vs Output Voltage (T_A = 25°C, V_A = 5 V)

6 Parameter Measurement Information

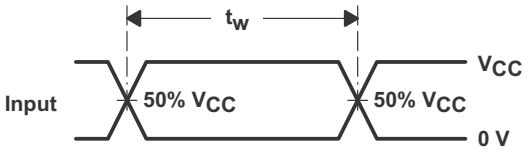


LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS

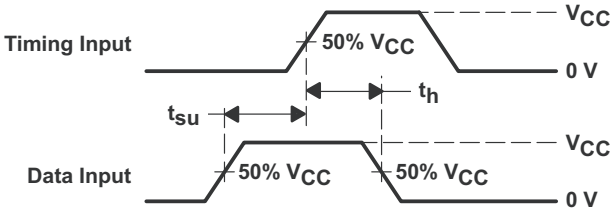


LOAD CIRCUIT FOR
3-STATE AND OPEN-DRAIN OUTPUTS

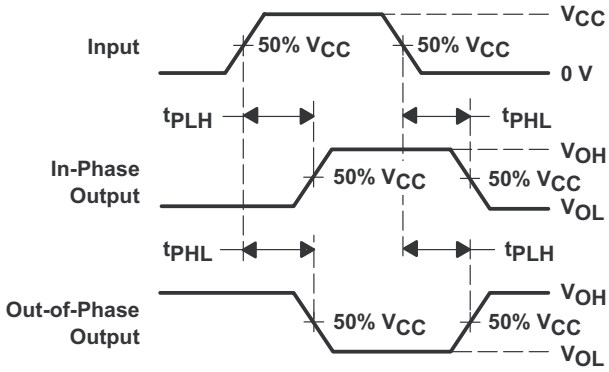
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND
Open Drain	V_{CC}



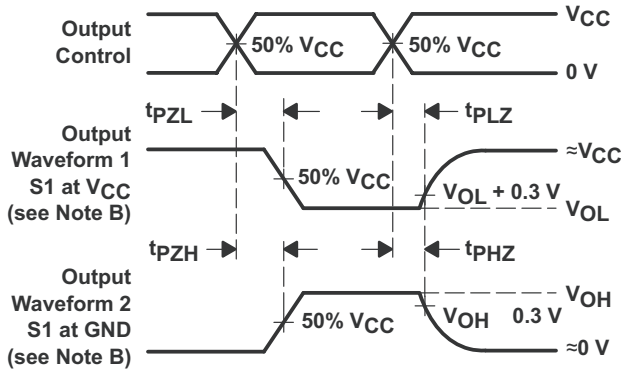
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 3 ns, t_f ≤ 3 ns.
D. The outputs are measured one at a time with one input transition per measurement.
E. All parameters and waveforms are not applicable to all devices.

図 6-1. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN74AHC1G08 device is a single 2-input positive-AND gate. The device performs the Boolean function Y = A ● B or Y = $\overline{A + B}$ in positive logic.

7.2 Functional Block Diagram

図 7-1. Logic Diagram (Positive Side)

7.3 Feature Description

The SN74AHC1G08 device has a wide operating V_{CC} range of 2 V to 5.5 V, which allows it to be used in a broad range of systems. The low propagation delay allows fast switching and higher operation speeds. In addition, the low-power consumption makes this device a good choice for portable and battery power-sensitive applications.

7.4 Device Functional Modes

表 7-1 lists the functional modes for SN74AHC1G08.

表 7-1. Function Table

INPUTS(1)		OUTPUT (2)
A	B	Y
H	H	H
L	X	L
X	L	L

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
(2) H = Driving High, L = Driving Low, Z = High Impedance State

8 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

8.1 Application Information

A common application for AND gates is their use in power sequencing. Power sequencing is often employed in applications that require a processor or other delicate device with specific voltage timing requirements in order to protect the device from malfunctioning. Using the SN74AHC1G08 to verify that the processor has turned on can protect it from any harmful signals.

8.2 Typical Application

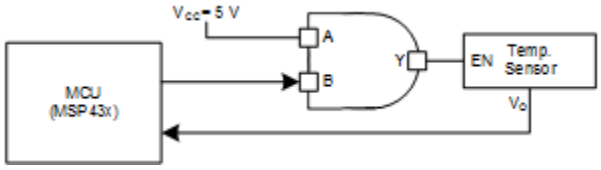


図 8-1. Power Sequencing Application

8.2.1 Design Requirements

The SN74AHC1G08 device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits.

The SN74AHC1G08 allows switching control of analog and digital signals with a digital control signal. All input signals should remain as close to either 0 V or V_{CC} as possible for optimal operation.

8.2.2 Detailed Design Procedure

1. Recommended input conditions:
   - For rise time and fall time specifications, see Δt/Δv in the *セクション 5.3* table.
   - For specified high and low levels, see V_{IH} and V_{IL} in the *セクション 5.3* table.
   - Inputs and outputs are overvoltage tolerant and can therefore go as high as 5.5 V at any valid V_{CC}.
2. Recommended output conditions:
   - Load currents should not exceed ±50 mA.
3. Frequency selection criterion:
   - The effects of frequency upon the device's power consumption should be studied in *CMOS Power Consumption and CPD Calculation*, SCAA035.
   - Added trace resistance and capacitance can reduce maximum frequency capability; follow the layout practices listed in the *セクション 8.4* section.

8.2.3 Application Curves

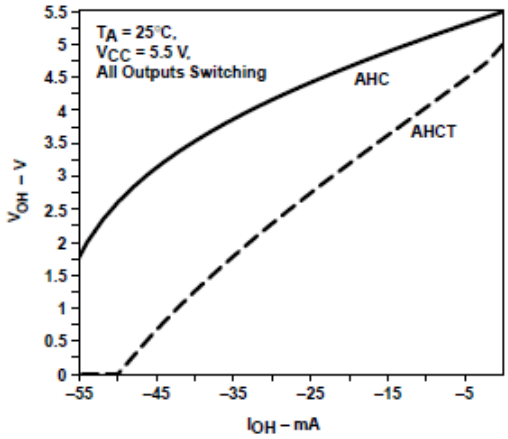


図 8-2. AHC Family V_{OH} vs I_{OH} at V_{CC} = 5.5 V

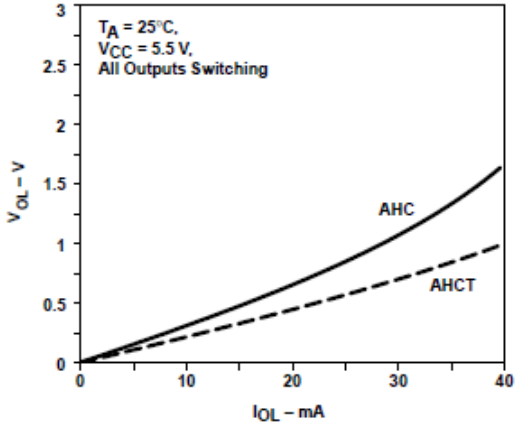


図 8-3. AHC Family V_{OL} vs I_{OL} at V_{CC} = 5.5 V

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *セクション 5.3* table.

Each V_{CC} terminal should have a bypass capacitor to prevent power disturbance. A 0.1-µF bypass capacitor is recommended for devices with a single supply. If multiple pins are labeled V_{CC}, then a 0.01-µF or 0.022-µF capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual-supply pins operating at different voltages, for example V_{CC} and V_{DD}, a 0.1-µF bypass capacitor is recommended for each supply pin. Use multiple bypass capacitors in parallel to reject different frequencies of noise. Capacitors with values of 0.1 µF and 1 µF are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. 図 8-4 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

8.4.1.1 Layout Example

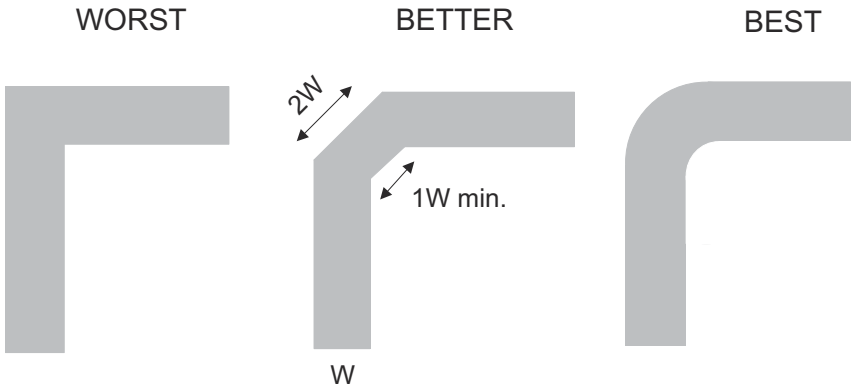


図 8-4. Trace Example

9 Device and Documentation Support

9.1 Documentation Support (Analog)

9.1.1 Related Documentation

For related documentation see the following:

- *Implications of Slow or Floating CMOS Inputs*, SCBA004
- *CMOS Power Consumption and CPD Calculation*, SCAA035
- *Selecting the Right Texas Instruments Signal Switch*, SZZA030

9.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

9.3 サポート・リソース

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9.5 静電気放電に関する注意事項

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ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

9.6 用語集

テキサス・インスツルメンツ用語集　この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision Q (October 2023) to Revision R (January 2024)	Page
• Updated RθJA values: DBV = 206 to 278, all values in °C/W	5

Changes from Revision P (March 2016) to Revision Q (October 2023)	Page
• ドキュメント全体にわたって表、図、相互参照の採番方法を更新	1
• Updated RθJA values: DCK = 252 to 289.2, all values in °C/W	5

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AHC1G08DBV3	ACTIVE	SOT-23	DBV	5	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-55 to 125	A08Y	Samples
SN74AHC1G08DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-55 to 125	(A083, A08G, A08J, A08L, A08S)	Samples
SN74AHC1G08DBVRE4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	A08G	Samples
SN74AHC1G08DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	A08G	Samples
SN74AHC1G08DBVTG4	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	A08G	Samples
SN74AHC1G08DCK3	ACTIVE	SC70	DCK	5	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-55 to 125	AEY	Samples
SN74AHC1G08DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-55 to 125	(1B9, AE3, AEG, AEJ, AEL, AES)	Samples
SN74AHC1G08DCKRE4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	AE3	Samples
SN74AHC1G08DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	AE3	Samples
SN74AHC1G08DCKTE4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	AE3	Samples
SN74AHC1G08DCKTG4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	AE3	Samples
SN74AHC1G08DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAU | NIPDAUAG	Level-1-260C-UNLIM	-55 to 125	(AEB, AES)	Samples
SN74AHC1G08DRLRG4	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-55 to 125	(AEB, AES)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF SN74AHC1G08 :

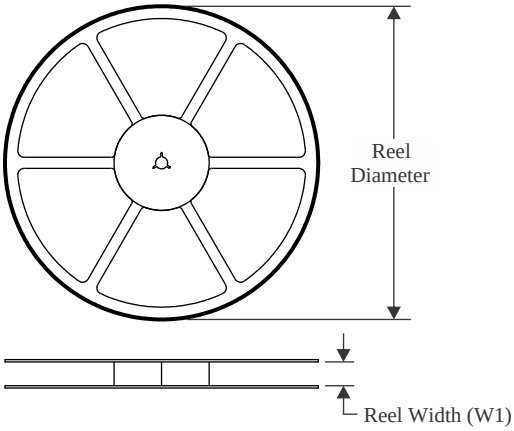
- Automotive : SN74AHC1G08-Q1

NOTE: Qualified Version Definitions:

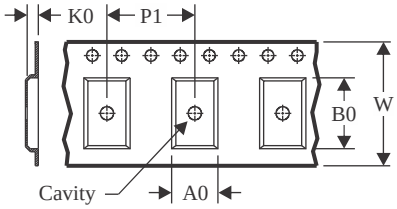
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

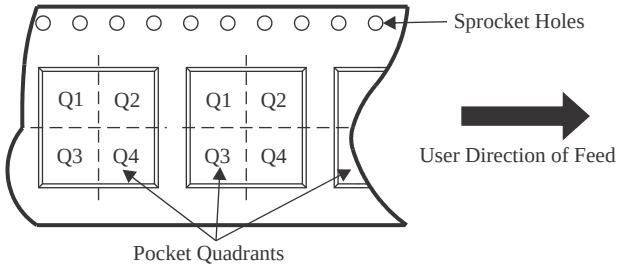


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

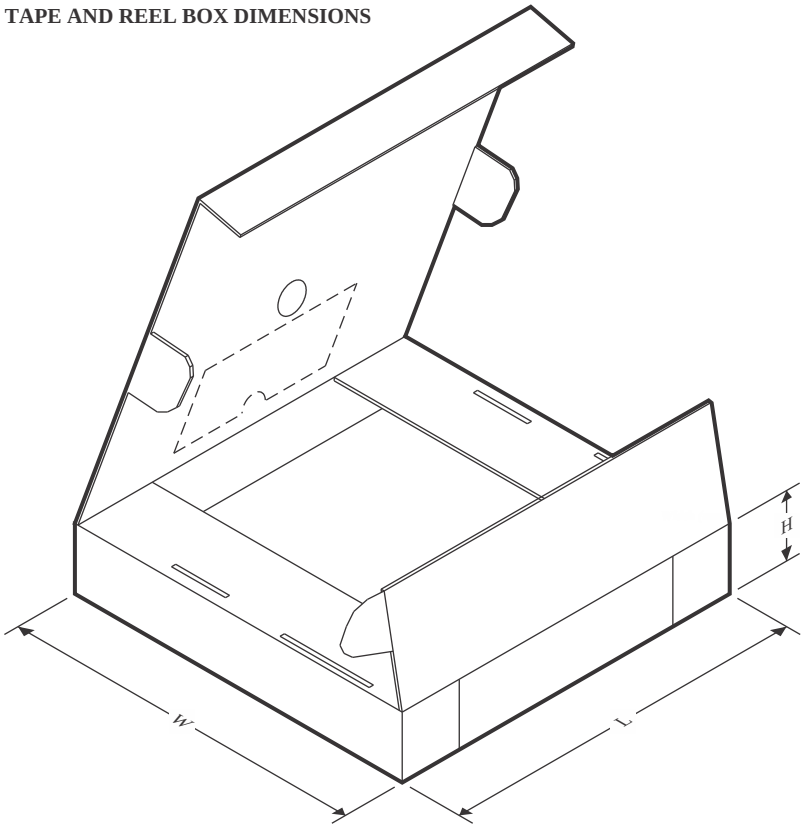
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC1G08DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74AHC1G08DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHC1G08DBVTG4	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHC1G08DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74AHC1G08DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74AHC1G08DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G08DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G08DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

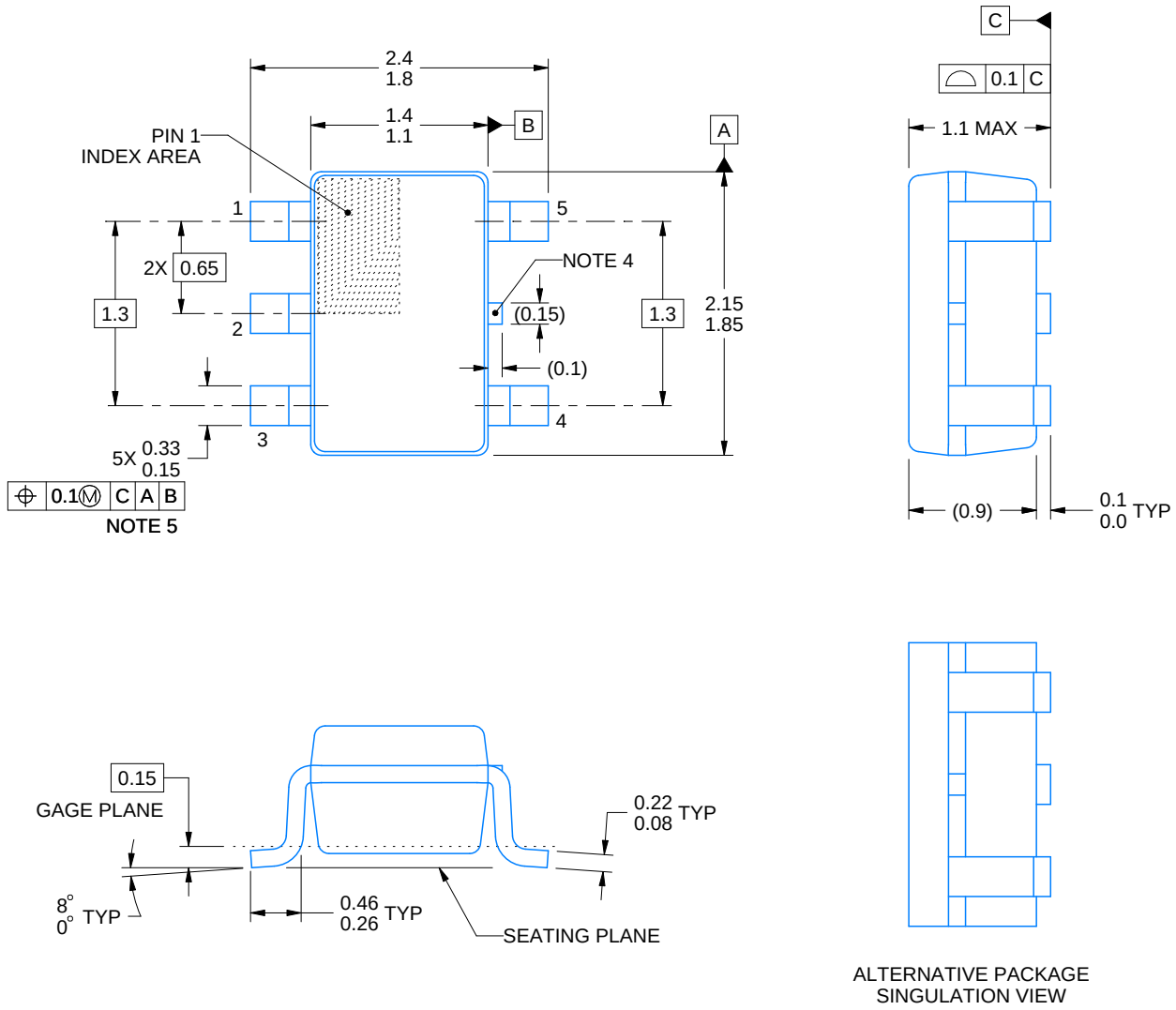
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AHC1G08DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHC1G08DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHC1G08DBVTG4	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74AHC1G08DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AHC1G08DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74AHC1G08DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AHC1G08DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0
SN74AHC1G08DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0

PACKAGE OUTLINE

DCK0005A

SOT - 1.1 max height

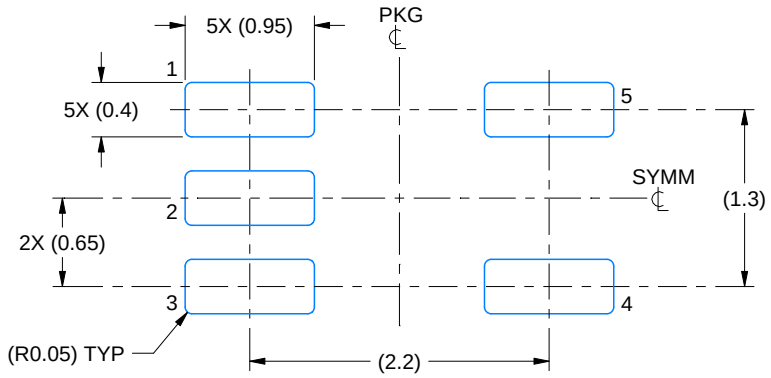
SMALL OUTLINE TRANSISTOR



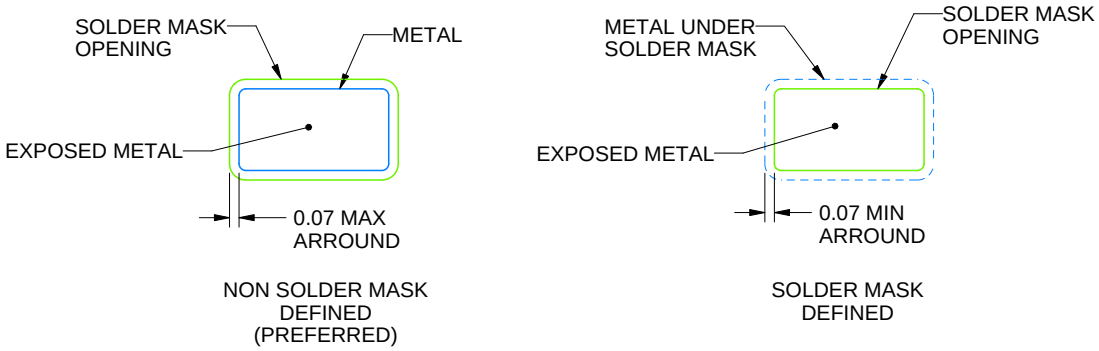
4214834/E 06/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

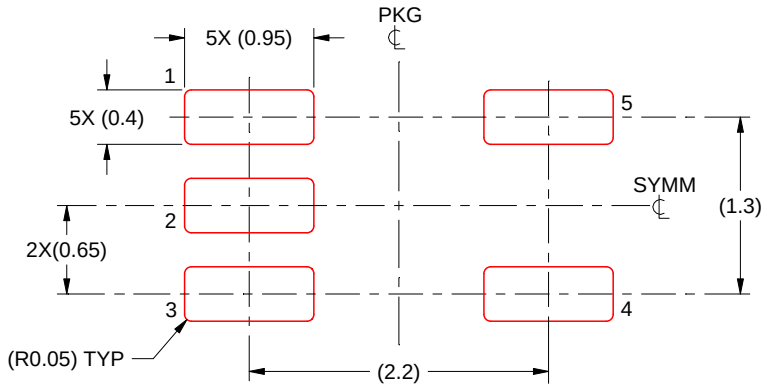


SOLDER MASK DETAILS

4214834/E 06/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/E 06/2024

NOTES: (continued)

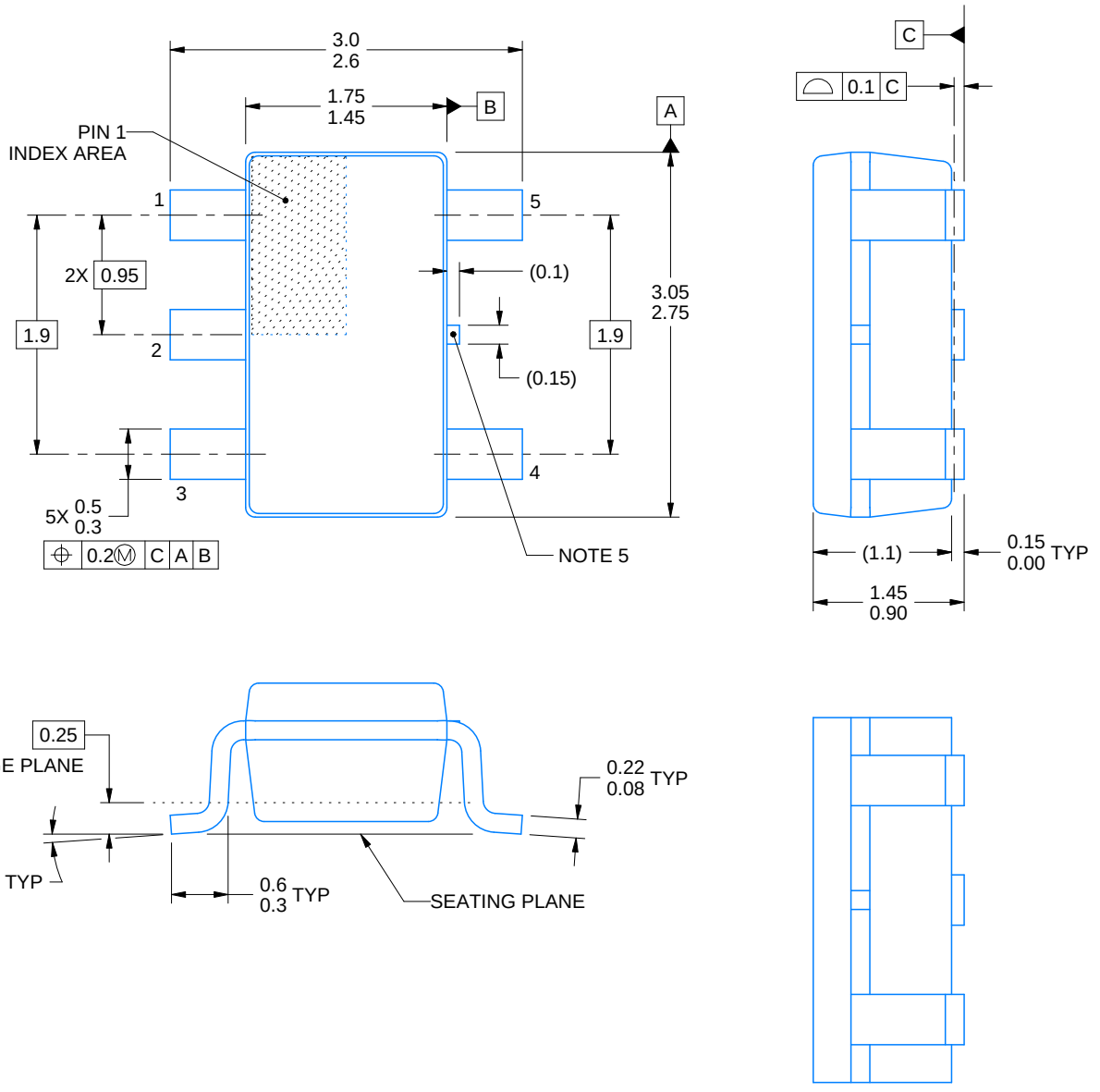
9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR

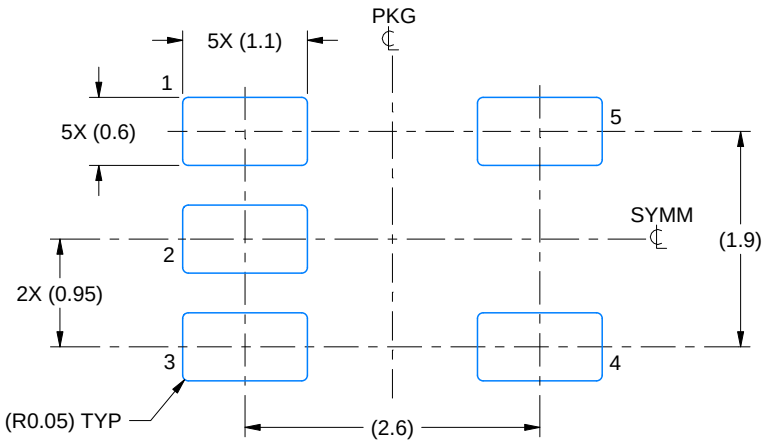


ALTERNATIVE PACKAGE SINGULATION VIEW

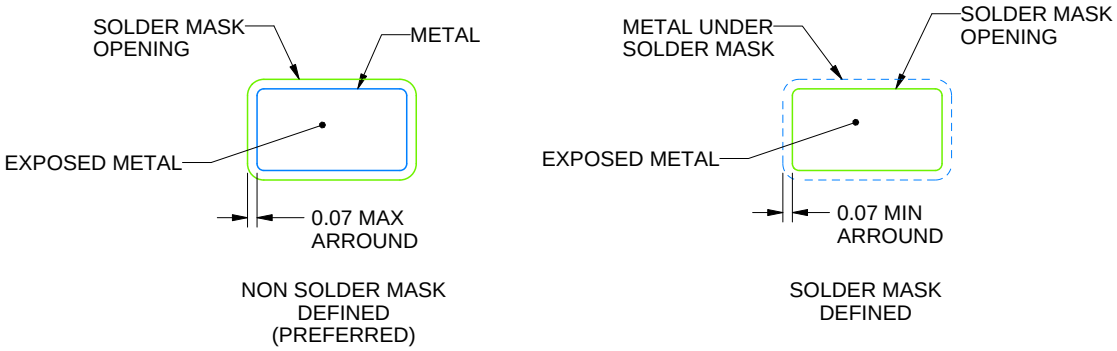
4214839/J 02/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

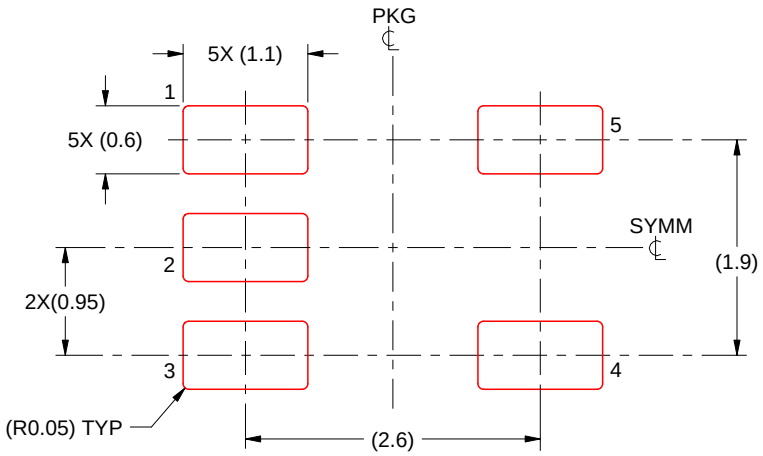


SOLDER MASK DETAILS

4214839/J 02/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/J 02/2024

NOTES: (continued)

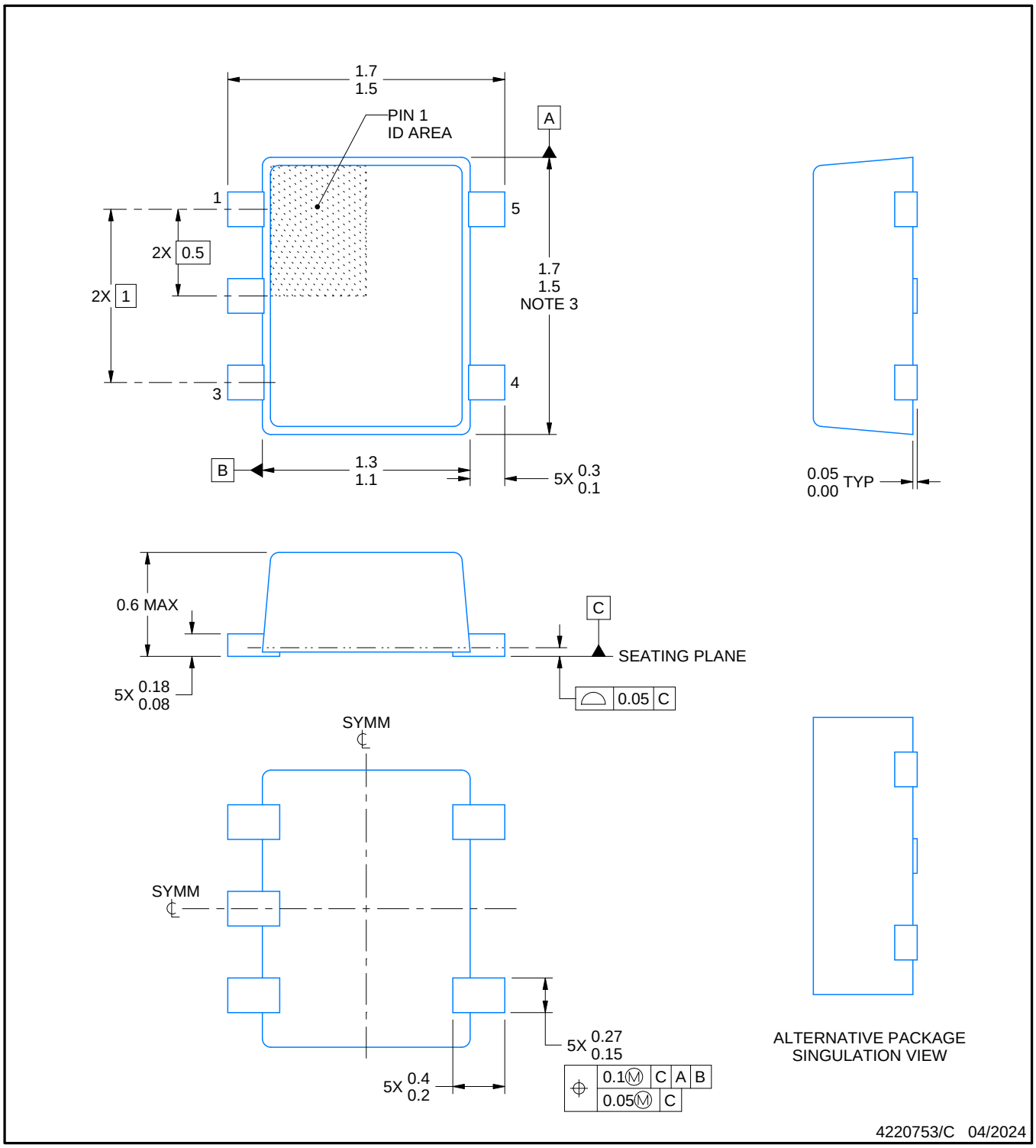
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DRL0005A

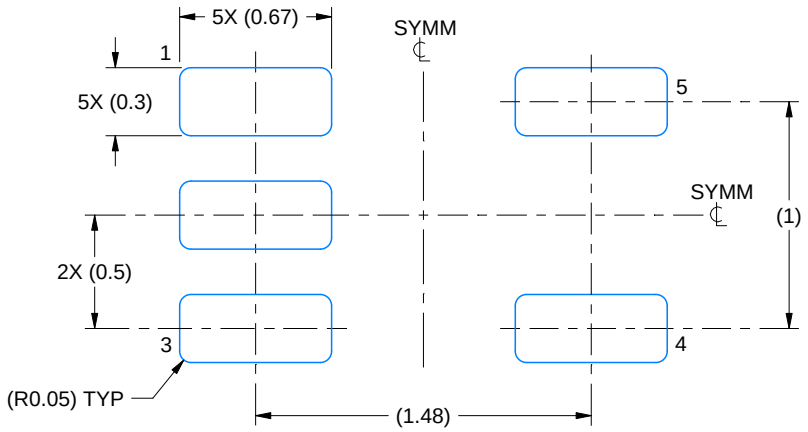
SOT - 0.6 mm max height

PLASTIC SMALL OUTLINE

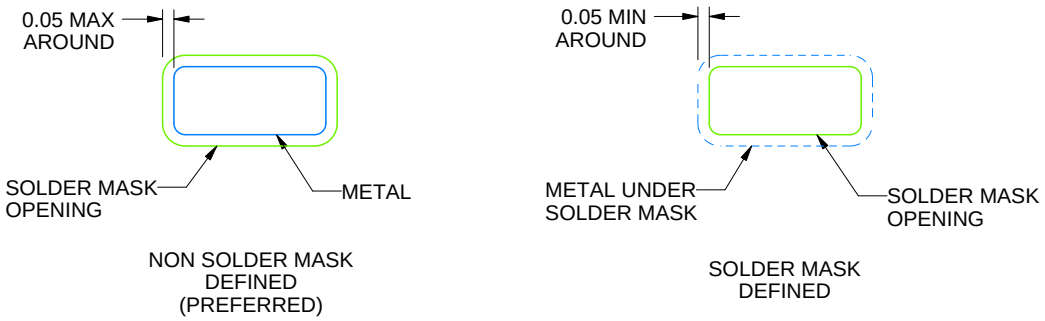


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-293 Variation UAAD-1



LAND PATTERN EXAMPLE
SCALE:30X

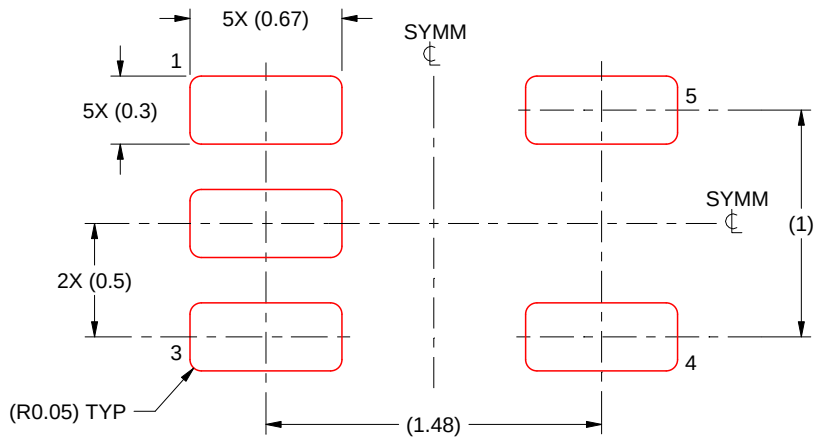


SOLDERMASK DETAILS

4220753/C 04/2024

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:30X

4220753/C 04/2024

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

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